

### Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

### Listing of Claims:

1. (Currently Amended) An SRAM comprising:  
a substrate;  
a pair of cross-coupled driver transistors formed over the substrate;  
a pair of access transistors;  
a pair of bit lines electrically connected to the cross-coupled driver transistors through the access transistors, respectively; and  
a bit line electrically connected to the pair of access transistors,  
wherein at least each of the cross-coupled driver transistors comprises a crystalline semiconductor film formed on an insulating surface over the substrate, said crystalline semiconductor film having a mono-domain region in which a channel formation region is formed, and  
wherein said crystalline semiconductor film comprises a source region and a drain region, and a metallic silicide is formed on the surface of said source region and said drain region.

2. (Original) The SRAM according to claim 1 wherein said mono-domain region includes substantially no grain boundary.

3. (Original) The SRAM according to claim 1 wherein any grain boundary included in said mono-domain region is electrically inactive.

4.(Currently Amended) An SRAM comprising:  
a substrate;  
a pair of cross-coupled driver transistors formed over the substrate;

a pair of access transistors;  
a pair of bit lines electrically connected to the cross-coupled driver transistors through the access transistors, respectively; and  
a bit line electrically connected to the pair of access transistors,  
wherein at least each of the access transistors comprises a crystalline semiconductor film formed on an insulating surface over the substrate, said crystalline semiconductor film having a mono-domain region in which a channel formation region is formed, and  
wherein said crystalline semiconductor film comprises a source region and a drain region,  
and a metallic silicide is formed on the surface of said source region and said drain region.

5. (Original) The SRAM according to claim 4 wherein said mono-domain region includes substantially no grain boundary.

6. (Original) The SRAM according to claim 4 wherein any grain boundary included in said mono-domain region is electrically inactive.

7. (Currently Amended) The SRAM comprising:  
a substrate;  
a pair of cross-coupled driver transistors formed over the substrate;  
a pair of access transistors;  
a pair of bit lines electrically connected to the cross-coupled driver transistors through the access transistors, respectively; and  
a bit line electrically connected to the pair of access transistors,  
wherein at least each of the cross-coupled driver transistors comprises a crystalline semiconductor film formed on an insulating surface over the substrate, said crystalline semiconductor film having a mono-domain region in which a channel formation region is formed,  
wherein said crystalline semiconductor film comprises a source region and a drain region,  
and a metallic silicide is formed on the surface of said source region and said drain region, and

wherein a crystallization direction of said crystalline semiconductor film is substantially in parallel with a major surface of the substrate.

8. (Original) The SRAM according to claim 7 wherein said mono-domain region includes substantially no grain boundary.

9. (Original) The SRAM according to claim 7 wherein any grain boundary included in said mono-domain region is electrically inactive.

10. (Currently Amended) An SRAM comprising:  
a substrate;  
a pair of cross-coupled driver transistors formed over the substrate;  
a pair of access transistors;  
a pair of bit lines electrically connected to the cross-coupled driver transistors through the access transistors, respectively; and

a bit line electrically connected to the pair of access transistors,  
wherein at least each of the access transistors comprises a crystalline semiconductor film formed on an insulating surface over the substrate, said crystalline semiconductor film having a mono-domain region in which a channel formation region is formed,

wherein said crystalline semiconductor film comprises a source region and a drain region, and a metallic silicide is formed on the surface of said source region and said drain region, and

wherein a crystallization direction of said crystalline semiconductor film is substantially in parallel with a major surface of the substrate.

11. (Original) The SRAM according to claim 10 wherein said mono-domain region includes substantially no grain boundary.

12. (Original) The SRAM according to claim 10 wherein any grain boundary included in said mono-domain region is electrically inactive.

13. (Currently Amended) An SRAM comprising:  
a substrate;  
an insulating film formed on the substrate, said insulating film having a protrusion extending in one direction;  
a pair of cross-coupled driver transistors formed over the substrate;  
a pair of access transistors;  
a pair of bit lines electrically connected to the cross-coupled driver transistors through the access transistors, respectively; and  
a bit line electrically connected to the pair of access transistors,  
wherein at least each of the cross-coupled driver transistors comprises a crystalline semiconductor film formed on the insulating film, said crystalline semiconductor film having a mono-domain region in which a channel formation region is formed, and  
wherein said crystalline semiconductor film comprises a source region and a drain region,  
and a metallic silicide is formed on the surface of said source region and said drain region.

14. (Original) The SRAM according to claim 13 wherein said mono-domain region includes substantially no grain boundary.

15. (Original) The SRAM according to claim 13 wherein any grain boundary included in said mono-domain region is electrically inactive.

16. (Currently Amended) An SRAM comprising:  
a substrate;  
an insulating film formed on the substrate, said insulating film having a protrusion extending in one direction;

a pair of cross-coupled driver transistors formed over the substrate;  
a pair of access transistors;  
a pair of bit lines electrically connected to the cross-coupled driver transistors through the access transistors, respectively; and  
a bit line electrically connected to the pair of access transistors,  
wherein at least each of the access transistors comprises a crystalline semiconductor film formed on the insulating film, said crystalline semiconductor film having a mono-domain region in which a channel formation region is formed, and  
wherein said crystalline semiconductor film comprises a source region and a drain region,  
and a metallic silicide is formed on the surface of said source region and said drain region.

17. (Original) The SRAM according to claim 16 wherein said mono-domain region includes substantially no grain boundary.

18. (Original) The SRAM according to claim 16 wherein any grain boundary included in said mono-domain region is electrically inactive.

19. (Original) A mobile computer comprising the SRAM according to claim 1.

20. (Original) A head-mount display comprising the SRAM according to claim 1.

21. (Original) A motor vehicle navigation comprising the SRAM according to claim 1.

22. (Currently Amended) A mobile phone ~~according~~ comprising the SRAM according to claim 1.

23. (Original) A video camera comprising the SRAM according to claim 1.

24. (Original) A projector comprising the SRAM according to claim 1.
25. (Original) A head-mount display comprising the SRAM according to claim 4.
26. (Original) A motor vehicle navigation comprising the SRAM according to claim 4.
27. (Currently Amended) A mobile phone ~~according~~ comprising the SRAM according to claim 4.
28. (Original) A video camera comprising the SRAM according to claim 4.
29. (Original) A projector comprising the SRAM according to claim 4.
30. (Original) A mobile computer comprising the SRAM according to claim 4.
31. (Original) A head-mount display comprising the SRAM according to claim 7.
32. (Original) A motor vehicle navigation comprising the SRAM according to claim 7.
33. (Currently Amended) A mobile phone ~~according~~ comprising the SRAM according to claim 7.
34. (Original) A video camera comprising the SRAM according to claim 7.
35. (Original) A projector comprising the SRAM according to claim 7.
36. (Original) A mobile computer comprising the SRAM according to claim 7.

37. (Original) A head-mount display comprising the SRAM according to claim 10.
38. (Original) A motor vehicle navigation comprising the SRAM according to claim 10.
39. (Currently Amended) A mobile phone ~~aeording~~ comprising the SRAM according to claim 10.
40. (Original) A video camera comprising the SRAM according to claim 10.
41. (Original) A projector comprising the SRAM according to claim 10.
42. (Original) A mobile computer comprising the SRAM according to claim 10.
43. (Original) A head-mount display comprising the SRAM according to claim 13.
44. (Original) A motor vehicle navigation comprising the SRAM according to claim 13.
45. (Currently Amended) A mobile phone ~~aeording~~ comprising the SRAM according to claim 13.
46. (Original) A video camera comprising the SRAM according to claim 13.
47. (Original) A projector comprising the SRAM according to claim 13.
48. (Original) A mobile computer comprising the SRAM according to claim 13.
49. (Original) A head-mount display comprising the SRAM according to claim 16.
50. (Original) A motor vehicle navigation comprising the SRAM according to claim 16.

51. (Currently Amended) A mobile phone ~~according~~ comprising the SRAM according to claim 16.

52. (Original) A video camera comprising the SRAM according to claim 16.

53. (Original) A projector comprising the SRAM according to claim 16.

54. (Original) A mobile computer comprising the SRAM according to claim 16.